

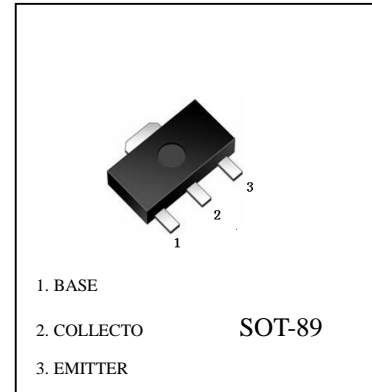
**FEATURES**

- High breakdown voltage and high current.  $BV_{CEO}=-80V, I_C=-1A$
- Good  $h_{FE}$  Linearity.
- Low  $V_{CE(sat)}$ .
- Complements the 2SD1898.

Marking: ZL

Maximum Ratings ( $T_a=25\text{ }^{\circ}\text{C}$  unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	-80	V
Collector-Emitter Voltage	$V_{CEO}$	-80	V
Emitter-Base Voltage	$V_{EBO}$	-5	V
Collector Current -Continuous	$I_C$	-1	A
Collector Power dissipation	$P_C$	500	mW
Junction Temperature	$T_J$	150	$^{\circ}\text{C}$
Storage Temperature	$T_{stg}$	-55to +150	$^{\circ}\text{C}$

**2SB1260(PNP)**


ELECTRICAL CHARACTERISTICS ( @  $T_a=25\text{ }^{\circ}\text{C}$  unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{CBO}$	$I_C=-50\mu\text{A}$ $I_E=0$	-80			V
Collector-emitter breakdown voltage	$V_{CEO}$	$I_C=-1\text{mA}$ $I_B=0$	-80			V
Emitter-base breakdown voltage	$V_{EBO}$	$I_E=-50\mu\text{A}$ $I_C=0$	-5			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=-60\text{V}$ $I_E=0$			-1	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=-4\text{V}$ , $I_C=0$			-1	$\mu\text{A}$
DC current gain	$h_{FE}$	$V_{CE}=-3\text{V}$ $I_C=-100\text{mA}$	82		390	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-500\text{mA}$ $I_B=-50\text{mA}$			-0.4	V
Transition frequency	$f_T$	$V_{CE}=-5\text{V}$ , $I_C=-50\text{mA}$ , $f=30\text{MHz}$		100		MHz
Output Capacitance	$C_{obo}$	$V_{CB}=-10\text{V}$ $f=1.0\text{MHz}$ $I_E=0$	-	25		pF

**2SB1260** Typical Characteristics

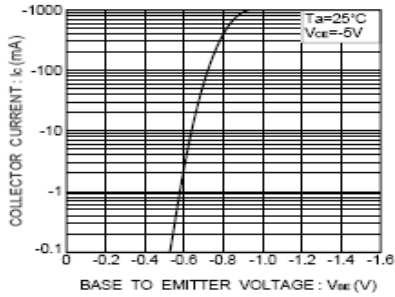


Fig.1 Grounded emitter propagation characteristics

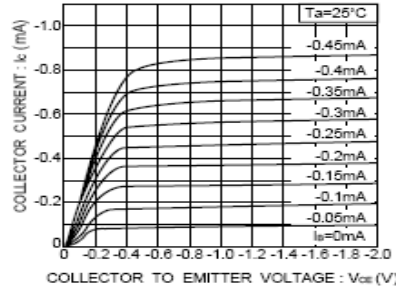


Fig.2 Grounded emitter output characteristics

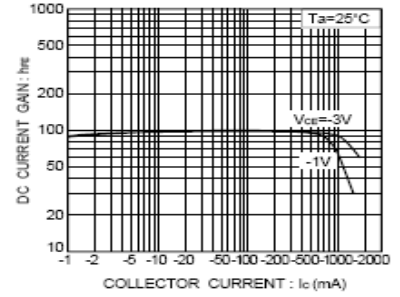


Fig.3 DC current gain vs. collector current

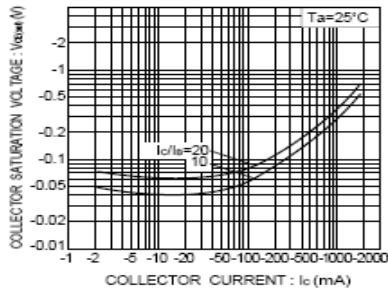


Fig.4 Collector-emitter saturation voltage vs. collector current

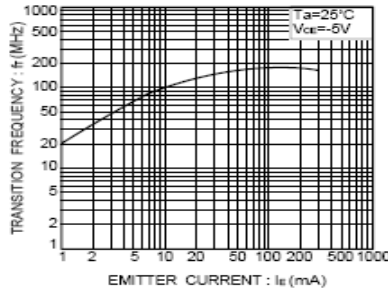


Fig.5 Gain bandwidth product vs. emitter current

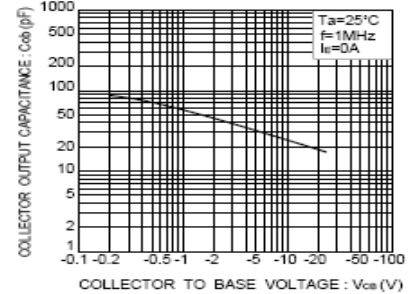


Fig.6 Collector output capacitance vs. collector-base voltage